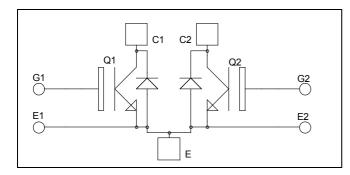


Dual common source Trench + Field Stop IGBT3 **Power Module**



G С E E2 G2

APTGT300DU60G

$V_{CES} = 600V$ $I_{\rm C} = 300 {\rm A}$ @ Tc = 80°C

Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop -
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior •
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile .
- **RoHS** Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	430	
	Continuous Conector Current	$T_C = 80^{\circ}C$	300	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	500	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1150	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	600A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				350	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 300A$	$T_j = 25^{\circ}C$		1.4	1.8	V
			$T_{j} = 150^{\circ}C$		1.5		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				500	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			24			
Coes	Output Capacitance				1.5		nF	
C _{res}	Reverse Transfer Capacitance	f = 1 MHz		0.75				
T _{d(on)}	Turn-on Delay Time	Inductive Switch	ning (25°C)		115		ns	
T _r	Rise Time	$V_{GE} = \pm 15V$			45			
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 300A$			200			
$T_{\rm f}$	Fall Time	$R_{G} = 1.8\Omega$			55			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 300A$			120		ns	
Tr	Rise Time				50			
T _{d(off)}	Turn-off Delay Time				250			
T _f	Fall Time	$R_G = 1.8\Omega$		70				
Г	T	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$V_{CE} = +15V$ T	$T_i = 25^{\circ}C$		1.5		T
Eon	Turn on Energy		$T_{j} = 150^{\circ}C$		2.7		mJ	
Б	$ E_{off} \text{Turn off Energy} \qquad I_{C} = 300 \text{A} \\ R_{G} = 1.8 \Omega $		$T_j = 25^{\circ}C$		8.55		mI	
$\mathbf{L}_{\mathrm{off}}$		$R_G = 1.8\Omega$	$T_{j} = 150^{\circ}C$		10.5		mJ	

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			150 400	μΑ
I _F	DC Forward Current		$T_j = 130 \text{ C}$ $T_c = 80^{\circ}\text{C}$		300	400	А
V _F	Diode Forward Voltage	$I_{\rm F} = 300 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$	$T_i = 25^{\circ}C$		1.5	1.9	V
v _F	Didde Forward Voltage		$T_{i} = 150^{\circ}C$		1.4		v
t _{rr}	Reverse Recovery Time	$I_{F} = 300A$ $V_{R} = 300V$ $di/dt = 3100A/\mu s$	$T_j = 25^{\circ}C$		130		ns
ι _{rr}			$T_{j} = 150^{\circ}C$		225		
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$		13.5		шС
			$T_{j} = 150^{\circ}C$		28.5		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		3.5		mJ
			$T_{j} = 150^{\circ}C$		7.1		1113

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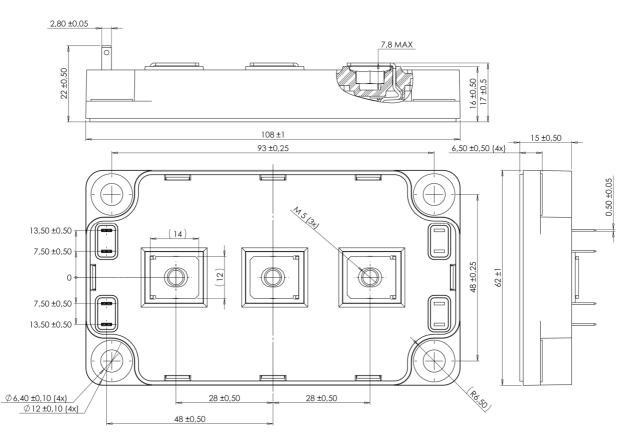


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Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance IGBT Diode				0.13	°C/W	
R _{th} JC			Diode			0.21	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		175	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

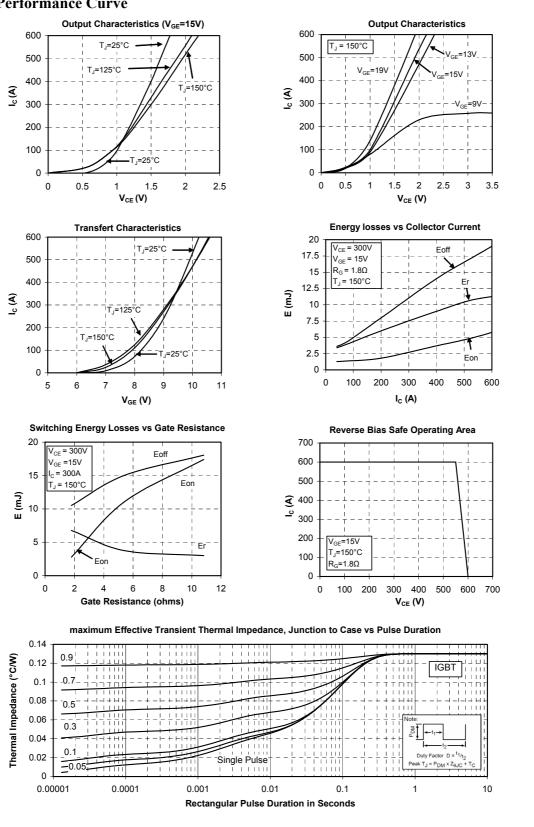
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Typical Performance Curve





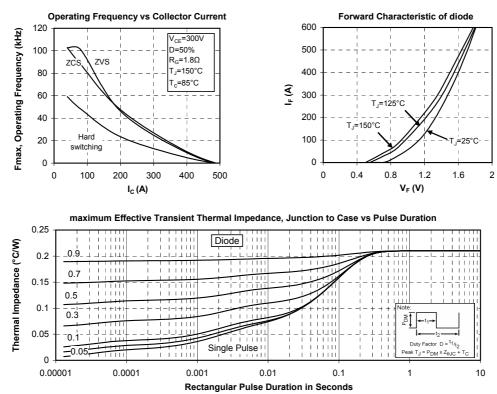
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